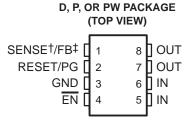
- Available in 5-V, 4.85-V, 3.3-V, 3.0-V, 2.75-V§, and 2.5-V Fixed-Output and Adjustable **Versions**
- Dropout Voltage <85 mV Max at $I_O = 100 \text{ mA (TPS7250)}$
- Low Quiescent Current, Independent of Load, 180 µA Typ
- 8-Pin SOIC and 8-Pin TSSOP Package
- Output Regulated to ±2% Over Full **Operating Range for Fixed-Output Versions**
- **Extremely Low Sleep-State Current, 0.5** μ**A Max**
- Power-Good (PG) Status Output

description

The TPS72xx family of low-dropout (LDO) voltage regulators offers the benefits of low-dropout voltage, micropower operation, and miniaturized packaging. These regulators feature extremely low dropout voltages and quiescent currents compared to conventional LDO regulators. Offered in small-outline integrated-circuit (SOIC) packages and 8-terminal thin shrink small-outline (TSSOP), the TPS72xx series devices are ideal for cost-sensitive designs and for designs where board space is at a premium.

A combination of new circuit design and process innovation has enabled the usual pnp pass transistor to be replaced by a PMOS device. Because the PMOS pass element behaves as a low-value resistor, the dropout voltage is very low - maximum of 85 mV at 100 mA of load current (TPS7250) - and is directly proportional to the load current (see Figure 1). Since the PMOS pass



†SENSE - Fixed voltage options only (TPS7225, TPS7228\$, TPS7230, TPS7233, TPS7248, and TPS7250)

‡FB – Adjustable version only (TPS7201)

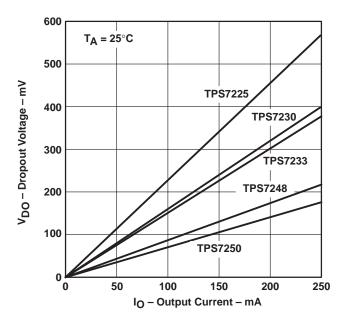


Figure 1. Typical Dropout Voltage Versus **Output Current**

element is a voltage-driven device, the quiescent current is very low (300 μA maximum) and is stable over the entire range of output load current (0 mA to 250 mA). Intended for use in portable systems such as laptops and cellular phones, the low-dropout voltage and micropower operation result in a significant increase in system battery operating life.

The TPS72xx also features a logic-enabled sleep mode to shut down the regulator, reducing guiescent current to $0.5 \,\mu\text{A}$ maximum at T $_{\text{I}}$ = 25°C. Other features include a power-good function that reports low output voltage and may be used to implement a power-on reset or a low-battery indicator.

The TPS72xx is offered in 2.5-V, 2.75-V \S , 3-V, 3.3-V, 4.85-V, and 5-V fixed-voltage versions and in an adjustable version (programmable over the range of 1.2 V to 9.75 V). Output voltage tolerance is specified as a maximum of 2% over line, load, and temperature ranges (3% for adjustable version).

§ This device is in the product preview stage of development. Please contact the local TI sales office for availability.



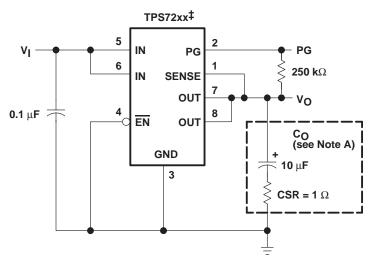
Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



AVAILABLE OPTIONS

т.	OUTPUT VOLTAGE (V)			P.	CHIP FORM		
ТЈ	MIN	TYP	MAX	SMALL OUTLINE (D)	PDIP (P)	TSSOP (PW)	(Y)
	4.9	5	5.1	TPS7250QD	TPS7250QP	TPS7250QPWR	TPS7250Y
	4.75	4.85	4.95	TPS7248QD	TPS7248QP	TPS7248QPWR	TPS7248Y
	3.23	3.3	3.37	TPS7233QD	TPS7233QP	TPS7233QPWR	TPS7233Y
-55°C to 150°C	2.94	3	3.06	TPS7230QD	TPS7230QP	TPS7230QPWR	TPS7230Y
	2.69	2.75	2.81	TPS7228QD†	TPS7228QP [†]	TPS7228QPWR [†]	TPS7228Y [†]
	2.45	2.5	2.55	TPS7225QD	TPS7225QP	TPS7225QPWR	TPS7225Y
	l	djustable V to 9.75		TPS7201QD	TPS7201QP	TPS7201QPWR	TPS7201Y

The D package is available taped and reeled. Add R suffix to device type (e.g., TPS7250QDR). The PW package is only available left-end taped and reeled. The TPS7201Q is programmable using an external resistor divider (see application information). The chip form is tested at 25°C.



 $[\]ddagger$ TPS7225Q, TPS7228Q \dagger , TPS7230Q, TPS7233Q, TPS7248Q, TPS7250Q (fixed-voltage options)

NOTE A: Capacitor selection is nontrivial. See application information section for details

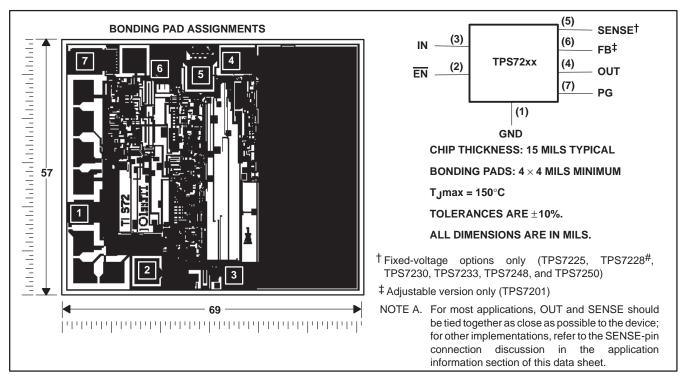
Figure 2. Typical Application Configuration

[†] This device is in the product preview stage of development. Please contact the local TI sales office for availability.

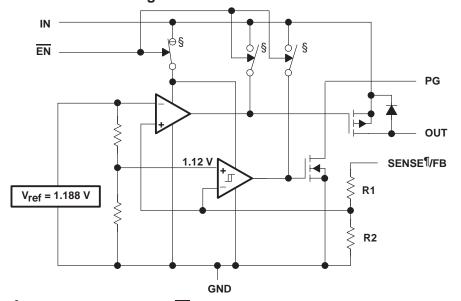


TPS72xx chip information

These chips, when properly assembled, display characteristics similar to the TPS72xxQ. Thermal compression or ultrasonic bonding may be used on the doped aluminum bonding pads. The chips may be mounted with conductive epoxy or a gold-silicon preform.



functional block diagram



RESISTOR DIVIDER OPTIONS

DEVICE	R1	R2	UNIT
TPS7201	0	8	Ω
TPS7225	257	233	kΩ
TPS7228#	306	233	kΩ
TPS7230	357	233	kΩ
TPS7233	420	233	kΩ
TPS7248	726	233	kΩ
TPS7250	756	233	kΩ

NOTE A: Resistors are nominal values only.

COMPONENT COUNT					
MOS transistors	108				
Bilpolar transistors	41				
Diodes	4				
Capacitors	15				
Resistors	75				

[#]This device is in the product preview stage of development. Please contact the local TI sales office for availability.



[§] Switch positions are shown with EN low (active).

For most applications, SENSE should be externally connected to OUT as close as possible to the device.

For other implementations, refer to the SENSE-pin connection discussion in application information section.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Input voltage range [‡] , V _I , PG, SENSE, EN	0.3 V to 11 V
Output current, IO	1.5 A
Continuous total power dissipation	See Dissipation Rating Tables 1 and 2
Operating virtual junction temperature range, T _J	–55°C to 150°C
Storage temperature range, T _{stq}	–65°C to 150°C
Lead temperature 1.6 mm (1/16 inch) from case for 10 second	s

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

DISSIPATION RATING TABLE 1 - FREE-AIR TEMPERATURE (see Note 1 and Figure 3)

PACKAGE	$T_{\mbox{A}} \le 25^{\circ}\mbox{C}$ POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 70°C POWER RATING	T _A = 85°C POWER RATING	T _A = 125°C POWER RATING
D	725 mW	5.8 mW/°C	464 mW	377 mW	145 mW
Р	1175 mW	8.74 mW/°C	782 mW	650 mW	301 mW
PW	525 mW	4.2 mW/°C	336 mW	273 mW	105 mW

DISSIPATION RATING TABLE 2 - CASE TEMPERATURE (see Note 1 and Figure 4)

PACKAGE	$T_C \le 25^{\circ}C$ POWER RATING	DERATING FACTOR ABOVE T _C = 25°C	T _C = 70°C POWER RATING	T _C = 85°C POWER RATING	T _C = 125°C POWER RATING
D	2063 mW	16.5 mW/°C	1320 mW	1073 mW	413 mW
Р	2738 mW	20.49 mW/°C	1816 mW	1508 mW	689 mW
PW	2900 mW	23.2 mW/°C	1856 mW	1508 mW	580 mW

NOTE 1: Dissipation rating tables and figures are provided for maintenance of junction temperature at or below absolute maximum of 150°C. For guidelines on maintaining junction temperature within the recommended operating range, see application information section.

MAXIMUM CONTINUOUS DISSIPATION

vs FREE-AIR TEMPERATURE

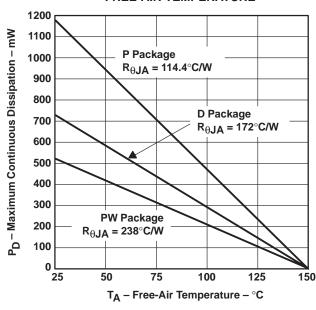


Figure 3

MAXIMUM CONTINUOUS DISSIPATION vs

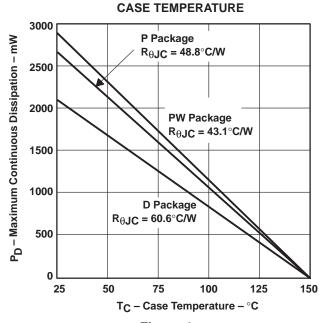


Figure 4



[‡] All voltage values are with respect to network ground terminal.

recommended operating conditions

		MIN	MAX	UNIT
	TPS7201Q	3	10	
	TPS7225Q	3.65	10	
	TPS7228Q [‡]	TBD	10	
Input voltage, V _I †	TPS7230Q	3.96	10	V
	TPS7233Q	3.98	10	
	TPS7248Q	5.24	10	
	TPS7250Q	5.41	10	
High-level input voltage at EN, VIH		2		V
Low-level input voltage at EN, V _{IL}			0.5	V
Output current, IO		0	250	mA
Operating virtual junction temperature, T _J		-40	125	°C

[†] Minimum input voltage defined in the recommended operating conditions is the maximum specified output voltage plus dropout voltage at the maximum specified load range. Since dropout voltage is a function of output current, the usable range can be extended for lighter loads. To calculate the minimum input voltage for the maximum load current used in a given application, use the following equation:

$$V_{I(min)} = V_{O(max)} + V_{DO(max load)}$$

Because the TPS7201 is programmable, $r_{DS(on)}$ should be used to calculate V_{DO} before applying the above equation. The equation for calculating V_{DO} from $r_{DS(on)}$ is given in Note 3 under the TPS7201 electrical characteristics table. The minimum value of 3 V is the absolute lower limit for the recommended input-voltage range for the TPS7201.



[‡] This device is in the product preview stage of development. Please contact the local TI sales office for availability.

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electrical characteristics, I $_{O}$ = 10 mA, \overline{EN} = 0 V, C $_{O}$ = 4.7 μF (CSR † = 1 Ω), SENSE/FB shorted to OUT (unless otherwise noted)

DADAMETER	TEST CONDITIONS‡		т.	TPS72xxQ			UNIT	
PARAMETER	TEST CON	IDITIONS+	TJ	MIN	TYP	MAX	UNII	
Cround current (active mode)	<u>EN</u> ≤ 0.5 V,	$V_I = V_O + 1 V_i$	25°C		180	225		
Ground current (active mode)	$0 \text{ mA} \le I_{\text{O}} \le 250 \text{ mA}$		-40°C to 125°C			325	μΑ	
Input ourment (standburmeds)	<u></u>	0.1/ < 1/ < 40.1/	25°C			0.5		
Input current (standby mode)	$\overline{EN} = V_{I},$	3 V ≤ V _I ≤ 10 V	-40°C to 125°C			1	μΑ	
Output ourront limit throubold	V= -0.V	\/· = 10 \/	25°C		0.6	1	Α	
Output current limit threshold	VO = 0 V	V _I = 10 V	-40°C to 125°C			1.5	A	
Pass-element leakage current in	EN V	0.1/ <1/ < 40.1/	25°C			0.5		
standby mode	$\overline{EN} = V_{I},$	3 V ≤ V _I ≤ 10 V	-40°C to 125°C			1	μΑ	
B01 1	V 40 V	Name of an austice	25°C			0.5	^	
PG leakage current	V _{PG} = 10 V,	Normal operation	-40°C to 125°C			0.5	μΑ	
Output voltage temperature coefficient			-40°C to 125°C		31	75	ppm/°C	
Thermal shutdown junction temperature					165		°C	
<u></u>	$3 \text{ V} \le \text{V}_{I} \le 6 \text{ V}$ $6 \text{ V} \le \text{V}_{I} \le 10 \text{ V}$		4000 to 40500	2			V	
EN logic high (standby mode)			-40°C to 125°C	2.7			1 ^v	
	21/21/2401/		25°C			0.5	V	
EN logic low (active mode)	3 V ≤ V _I ≤ 10 V		-40°C to 125°C			0.5	V	
EN hysteresis voltage			25°C		50		mV	
=	0)/ <)/ < 40)/		25°C	-0.5		0.5		
EN input current	$0 \text{ V} \leq \text{V}_{\text{I}} \leq 10 \text{ V}$		-40°C to 125°C	-0.5		0.5	μΑ	
Minimum V. for active need algorithm			25°C		1.9	2.5	V	
Minimum V _I for active pass element			-40°C to 125°C			2.5	·	
Minimum V. for valid DC	l= = 200 A		25°C		1.1	1.5	V	
Minimum V _I for valid PG	IpG = 300 μA		-40°C to 125°C			1.9	·	

[†] CSR(compensation series resistance) refers to the total series resistance, including the equivalent series resistance (ESR) of the capacitor, any series resistance added externally, and PWB trace resistance to CO.

[‡] Pulse-testing techniques are used to maintain virtual junction temperature as close as possible to ambient temperature; thermal effects must be taken into account separately.

TPS7201Q electrical characteristics, I_O = 10 mA, V_I = 3.5 V, \overline{EN} = 0 V, C_O = 4.7 μF (CSR[†] = 1 Ω), FB shorted to OUT at device leads (unless otherwise noted)

DARAMETER				TPS7201Q		LINUT	
PARAMETER	IEST COI	NDITIONS‡	ТЈ	MIN	TYP	MAX	UNIT
Reference voltage (measured	V _I = 3.5 V,	I _O = 10 mA	25°C		1.188		V
at FB with OUT connected to FB)	$3 \text{ V} \le \text{V}_{\text{I}} \le 10 \text{ V},$ See Note 2	$5 \text{ mA} \le I_O \le 250 \text{ mA},$	-40°C to 125°C	1.152		1.224	V
Reference voltage temperature coefficient			-40°C to 125°C		31	75	ppm/°C
	V _I = 2.4 V,§	$50 \mu A \le I_O \le 100 mA$	25°C		2.1		
	V _I = 2.4 V,§	$100 \text{ mA} \le I_{O} \le 200 \text{ mA}$	25°C		2.9		
Pass-element series	V. 00V	50 ·· A < l - < 050 ·· A	25°C		1.6	2.7	
resistance (see Note 3)	V _I = 2.9 V,	$50 \ \mu\text{A} \le I_{O} \le 250 \ \text{mA}$	-40°C to 125°C			4.5	Ω
	V _I = 3.9 V,	$50 \ \mu\text{A} \le I_{O} \le 250 \ \text{mA}$	25°C		1		
	V _I = 5.9 V,	$50 \ \mu A \le I_O \le 250 \ mA$	25°C		0.8		
Input regulation	V _I = 3 V to 10 V,	50 μ A ≤ I _O ≤ 250 mA,	25°C			23	mV
input regulation	See Note 2		-40°C to 125°C			36	IIIV
	I _O = 5 mA to 250 mA, See Note 2	$3 \text{ V} \le \text{V}_{\text{I}} \le 10 \text{ V},$	25°C		15	25	mV
Output regulation			-40°C to 125°C			36	
Output regulation	$I_O = 50 \mu A$ to 250 mA, See Note 2	$3 \text{ V} \le \text{V}_{I} \le 10 \text{ V},$	25°C		17	27	
			-40°C to 125°C			43	
		$I_{O} = 50 \mu A$ $I_{O} = 250 \text{ mA},$	25°C	49	60		dB
Ripple rejection	f = 120 Hz		-40°C to 125°C	32			
Ripple rejection	T = 120 HZ		25°C	45	50		
		See Note 2	-40°C to 125°C	30			
Output noise spectral density	f = 120 Hz		25°C		2		μV/√Hz
		C _O = 4.7 μF	25°C		235		
Output noise voltage	10 Hz \leq f \leq 100 kHz, CSR [†] = 1 Ω	C _O = 10 μF	25°C		190		μVrms
	001(1 = 1 32	C _O = 100 μF	25°C		125		
PG trip-threshold voltage¶	V _{FB} voltage decreasino	g from above V _{PG}	-40°C to 125°C		0.95 × VFB(nom)		V
PG hysteresis voltage¶	Measured at V _{FB}		25°C		12		mV
DO	4004	V 0.40 V	25°C		0.1	0.4	
PG output low voltage¶	I _{PG} = 400 μA,	V _I = 2.13 V	-40°C to 125°C			0.4	'
ED input ourrant			25°C	-10	0.1	10	Λ
FB input current			-40°C to 125°C	-20		20	nA

[†] CSR refers to the total series resistance, including the ESR of the capacitor, any series resistance added externally, and PWB trace resistance

NOTES: 2. When $V_1 < 2.9 \text{ V}$ and $I_0 > 100 \text{ mA}$ simultaneously, pass element $r_{DS(on)}$ increases (see Figure 10) to a point such that the resulting dropout voltage prevents the regulator from maintaining the specified tolerance range.

3. To calculate dropout voltage, use equation:

 $V_{DO} = I_O \cdot r_{DS(on)}$

 $r_{DS(on)}$ is a function of both output current and input voltage. The parametric table lists $r_{DS(on)}$ for $V_I = 2.4 \text{ V}$, 2.9 V, 3.9 V, and 5.9 V, which corresponds to dropout conditions for programmed output voltages of 2.5 V, 3 V, 4 V, and 6 V, respectively. For other programmed values, refer to Figures 10 and 11.



[‡] Pulse-testing techniques are used to maintain virtual junction temperature as close as possible to ambient temperature; thermal effects must be taken into account separately.

[§] This voltage is not recommended.

 $[\]P$ Output voltage programmed to 2.5 V with closed-loop configuration (see application information).

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TPS7225Q electrical characteristics, I $_{O}$ = 10 mA, V $_{I}$ = 3.5 V, \overline{EN} = 0 V, C $_{O}$ = 4.7 μF (CSR † = 1 Ω), SENSE shorted to OUT (unless otherwise noted)

PARAMETER	TEST CON	IDITIONET	т.		TPS7225Q		UNIT
PARAMETER	TEST CON	DITION5+	TJ	MIN	TYP	MAX	UNII
Output voltage	V _I = 3.5 V,	$I_O = 10 \text{ mA}$	25°C		2.5		V
Output voltage	$3.5 \text{ V} \le \text{V}_{\text{I}} \le 10 \text{ V},$	$5~\text{mA} \leq I_{\mbox{\scriptsize O}} \leq 250~\text{mA}$	-40°C to 125°C	2.45		2.55	V
Dropout voltogo	IO = 250 mA,	V _I = 2.97 V	25°C		560	850	mV
Dropout voltage	10 = 230 IIIA,	V = 2.97 V	-40°C to 125°C			1.1	V
Pass-element series resistance	(2.97 V – V _O)/I _O ,	V _I = 2.97 V,	25°C		2.24	3.4	Ω
1 ass-element series resistance	I _O = 250 mA		-40°C to 125°C			3.84	22
Input regulation	V _I = 3.5 V to 10 V,	50 μA ≤ I _O ≤ 250 mA	25°C		9	27	mV
Input regulation	v = 3.5 v to 10 v,	30 μA ≤ 10 ≤ 230 IIIA	-40°C to 125°C			33	IIIV
	I _O = 5 mA to 250 mA,	35 \/ < \/, < 10 \/	25°C		28	36	
Output regulation	10 = 5 mA to 250 mA,	3.5 V ≤ V ≤ 10 V	-40°C to 125°C			60	mV
Output regulation	$I_O = 50 \mu A \text{ to } 250 \text{ mA},$	3.5 V ≤ V _I ≤ 10 V	25°C		24	41	
			-40°C to 125°C			73	
	f = 120 Hz	$I_O = 50 \mu A$ $I_O = 250 \text{ mA}$	25°C	47	58		dB
Ripple rejection			-40°C to 125°C	45			
Ripple rejection			25°C	40	46		
			-40°C to 125°C	38			
Output noise spectral density	f = 120 Hz		25°C		2		μV/√ Hz
	40.11 - 46.4400.111	C _O = 4.7 μF	25°C		248		
Output noise voltage	10 Hz \leq f \leq 100 kHz, CSR [†] = 1 Ω	C _O = 10 μF	25°C		200		μVrms
		C _O = 100 μF	25°C		130		
PG trip-threshold voltage	VO voltage decreasing	from above VpG	-40°C to 125°C		0.95 × VO(nom)		V
PG hysteresis voltage			25°C		50		mV
DC autaut lauvualta aa	1 10 1	V 0.40.V	25°C		0.3	0.44	
PG output low voltage	$I_{PG} = 1.2 \text{ mA},$	V _I = 2.13 V	-40°C to 125°C			0.5	V

[†] CSR refers to the total series resistance, including the ESR of the capacitor, any series resistance added externally, and PWB trace resistance to Co.

[‡] Pulse-testing techniques are used to maintain virtual junction temperature as close as possible to ambient temperature; thermal effects must be taken into account separately.

TPS7201Q, TPS7225Q, TPS7228Q, TPS7230Q TPS7233Q, TPS7248Q, TPS7250Q, TPS72xxY MICROPOWER LOW-DROPOUT (LDO) VOLTAGE REGULATORS SLVS102F - MARCH 1995 - REVISED NOVEMBER 1998

TPS7228Q electrical characteristics, I_O = 10 mA, V_I = 3.75 V, $\overline{\text{EN}}$ = 0 V, C_O = 4.7 μF (CSR[†] = 1 Ω), SENSE shorted to OUT (unless otherwise noted)

PARAMETER	TEST COM	TEST CONDITIONS‡			PS7228	Q	UNIT
PARAMETER	TEST CON	IDITIONS+	ТЈ	MIN	TYP	MAX	UNII
Output voltage	V _I = 3.75 V,	I _O = 10 mA	25°C		2.75		. v
Culput voltage	$3.75 \text{ V} \le \text{V}_{I} \le 10 \text{ V},$	$5 \text{ mA} \le I_{O} \le 250 \text{ mA}$	-40°C to 125°C	2.69		2.81	ı v
	IO = 10 mA,	V _I = 2.69 V	25°C		TBD		
	10 = 10 IIIA,	V = 2.09 V	-40°C to 125°C			TBD	
Dropout voltage	IO = 100 mA,	V _I = 2.69 V	25°C		TBD		mV
Diopout voltage	10 = 100 1117,	V = 2.09 V	-40°C to 125°C			TBD] ''''
	IO = 250 mA,	V _I = 2.69 V	25°C		TBD		
	10 = 230 IIIA,	V = 2.09 V	-40°C to 125°C			TBD	
Pass-element series resistance	(2.69 V – V _O)/I _O ,	V _I = 2.69 V,	25°C		TBD		Ω
r ass-element selles resistance	$I_O = 250 \text{ mA}$		-40°C to 125°C			TBD	52
Input regulation	V _I = 3.75 V to 10 V,	$50 \mu\text{A} \le \text{I}_{\text{O}} \le 250 \text{mA}$	25°C		TBD		mV
Input regulation			-40°C to 125°C			TBD	IIIV
	$I_0 = 5 \text{ mA to } 250 \text{ mA},$	$3.75 \text{ V} \le \text{V}_{\text{I}} \le 10 \text{ V}$	25°C		TBD		mV
Output regulation			-40°C to 125°C			TBD	
Output regulation	In FO A to 250 mA	3.75 V ≤ V _I ≤ 10 V	25°C		TBD		
	$I_O = 50 \mu A \text{ to } 250 \text{ mA},$		-40°C to 125°C			TBD	
		ΙΟ = 50 μΑ	25°C		TBD		
Dinale rejection	f = 120 Hz	ΙΟ = 50 μΑ	-40°C to 125°C		TBD		
Ripple rejection	1 = 120 HZ	10 050 m A	25°C		TBD		dB
		I _O = 250 mA	-40°C to 125°C		TBD		
Output noise spectral density	f = 120 Hz		25°C		TBD		μV/√Hz
		$C_{O} = 4.7 \mu F$	25°C		TBD		
Output noise voltage	10 Hz \leq f \leq 100 kHz, CSR [†] = 1 Ω	C _O = 10 μF	25°C		TBD		μVrms
	05/(1 = 1.52	C _O = 100 μF	25°C		TBD		1
PG trip-threshold voltage	V _O voltage decreasing	from above V _{PG}	-40°C to 125°C		TBD		V
PG hysteresis voltage			25°C		TBD		mV
7			25°C			TBD	
PG output low voltage	$I_{PG} = 1.2 \text{ mA},$	$V_{I} = 2.34 \text{ V}$	-40°C to 125°C			TBD	V
			+0 0 to 120 0			יטטי	

[†] CSR refers to the total series resistance, including the ESR of the capacitor, any series resistance added externally, and PWB trace resistance

[‡] Pulse-testing techniques are used to maintain virtual junction temperature as close as possible to ambient temperature; thermal effects must be taken into account separately.

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TPS7230Q electrical characteristics, I $_{O}$ = 10 mA, V $_{I}$ = 4 V, \overline{EN} = 0 V, C $_{O}$ = 4.7 μF (CSR † = 1 Ω), SENSE shorted to OUT (unless otherwise noted)

DADAMETER	TEST CON	т.	Т	PS7230Q		UNIT	
PARAMETER	TEST CON	DITIONS+	ТЈ	MIN	TYP	MAX	UNII
Output voltage	V _I = 4 V,	$I_O = 10 \text{ mA}$	25°C		3		V
Output voltage	$4 \text{ V} \le \text{V}_{I} \le 10 \text{ V},$	$5~\text{mA} \leq I_{\mbox{\scriptsize O}} \leq 250~\text{mA}$	-40°C to 125°C	2.94		3.06	V
	1 400 ··· A	V _I = 2.97 V	25°C		145	185	
Description to the man	I _O = 100 mA,	V = 2.97 V	-40°C to 125°C			270	mV
Dropout voltage	I _O = 250 mA,	V _I = 2.97 V	25°C		390	502	IIIV
	10 = 250 MA,	V = 2.97 V	-40°C to 125°C			900	
Pass-element series resistance	(2.97 V – V _O)/I _O ,	V _I = 2.97 V,	25°C		1.56	2.01	Ω
Fass-element series resistance	I _O = 250 mA	·	-40°C to 125°C			3.6	52
Input regulation	V _I = 4 V to 10 V,	0.1/ 50 4 4 4 6504	25°C		9	27	mV
Input regulation	V = 4 V tO 10 V,	$50 \mu\text{A} \le \text{I}_{\text{O}} \le 250 \text{mA}$	-40°C to 125°C			33	IIIV
	I _O = 5 mA to 250 mA,	4 V ≤ V _I ≤ 10 V	25°C		34	45	mV
Output regulation			-40°C to 125°C			74	
Output regulation	$I_O = 50 \mu A \text{ to } 250 \text{ mA},$	4 V ≤ V _I ≤ 10 V	25°C		42	60	
			-40°C to 125°C			98	
		ΙΟ = 50 μΑ	25°C	45	56		
Dinnle rejection	f = 120 Hz		-40°C to 125°C	44			
Ripple rejection	T = 120 HZ		25°C	40	45		dB
		I _O = 250 mA	-40°C to 125°C	38			1
Output noise spectral density	f = 120 Hz		25°C		2		μV/√ Hz
		$C_O = 4.7 \mu F$	25°C		256		
Output noise voltage	10 Hz \leq f \leq 100 kHz, CSR [†] = 1 Ω	C _O = 10 μF	25°C		206		μVrms
	031(1 = 1 32	C _O = 100 μF	25°C		132		
PG trip-threshold voltage	VO voltage decreasing t	from above V _{PG}	-40°C to 125°C		0.95 × VO(nom)		V
PG hysteresis voltage			25°C		50		mV
PO 1 11 11			25°C		0.25	0.44	.,
PG output low voltage	Ipg = 1.2 mA,	V _I = 2.55 V	-40°C to 125°C			0.44	V

[†]CSR refers to the total series resistance, including the ESR of the capacitor, any series resistance added externally, and PWB trace resistance to CO.

[‡] Pulse-testing techniques are used to maintain virtual junction temperature as close as possible to ambient temperature; thermal effects must be taken into account separately.

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TPS7233Q electrical characteristics, I $_{O}$ = 10 mA, V $_{I}$ = 4.3 V, \overline{EN} = 0 V, C $_{O}$ = 4.7 μF (CSR † = 1 Ω), SENSE shorted to OUT (unless otherwise noted)

2.2.445	TEOT 001	DITIONS [‡]			TPS7233Q		
PARAMETER	TEST CON	DITIONS+	TJ	MIN	TYP	MAX	UNIT
Output voltage	V _I = 4.3 V,	I _O = 10 mA	25°C		3.3		\ \
Output voltage	$4.3 \text{ V} \le \text{V}_{I} \le 10 \text{ V},$	$5 \text{ mA} \le I_O \le 250 \text{ mA}$	-40°C to 125°C	3.23		3.37	V
	I _O = 10 mA,	V _I = 3.23 V	25°C		14	20	
	10 = 10 IIIA,	V = 3.23 V	-40°C to 125°C			30	
Dropout voltage	I _O = 100 mA,	V _I = 3.23 V	25°C		140	180	m\/
Dropout voltage	10 = 100 mz,	V = 3.23 V	-40°C to 125°C			232] '''V
	I _O = 250 mA,	V _I = 3.23 V	25°C		360	460	
	10 = 250 IIIA,	V = 3.23 V	-40°C to 125°C			610	WNIT V mV Ω mV dB μV/\(\sqrt{Hz}\) μVrms V mV
Pass-element series resistance	(3.23 V – V _O)/I _O ,	V _I = 3.23 V,	25°C		1.5	1.84	
r ass-element series resistance	I _O = 250 mA		-40°C to 125°C			2.5	22
Input regulation	V _I = 4.3 V to 10 V,	50 μA ≤ I _O ≤ 250 mA	25°C		8	25	m\/
Input regulation	V = 4.3 V to 10 V,	50 μA ≤ 1O ≤ 250 IIIA	-40°C to 125°C			33	IIIV
	$I_{O} = 5 \text{ mA to } 250 \text{ mA},$	4 2 V < V < 10 V	25°C		32	42	
Output regulation	10 = 3 111A to 230 111A,	4.5 V \(\) V \(\) \(\)	-40°C to 125°C			71	m\/
	lo = 50 u \ to 250 m \	A, 4.3 V ≤ V _I ≤ 10 V 25°C 41	55] '''			
	$10 = 30 \mu\text{A}$ to 230 mA,	4.5 V \(\) V \(\) \(\) \(\)	-40°C to 125°C			98	mV
		ΙΟ = 50 μΑ	25°C	40	52		
Ripple rejection	f = 120 Hz	ΙΟ = 50 μΑ	-40°C to 125°C	38			4B
Ripple rejection	1 = 120112	I _O = 250 mA	25°C	35	44		ub
		10 = 250 IIIA	-40°C to 125°C	33			
Output noise spectral density	f = 120 Hz		25°C		2		μV/√ Hz
		$C_O = 4.7 \mu F$	25°C		265		
Output noise voltage	10 Hz \leq f \leq 100 kHz, CSR \dagger = 1 Ω	C _O = 10 μF	25°C		212		μVrms
	001(1 = 1 52	C _O = 100 μF	25°C		135		
PG trip-threshold voltage	V _O voltage decreasing from above V _{PG}		-40°C to 125°C		$\begin{array}{c} 0.95 \times \\ \text{VO(nom)} \end{array}$		V
PG hysteresis voltage			25°C		32		mV
PG output low voltage	Inc - 1.2 mA	\/ı = 2.9.\/	25°C		0.22	0.4	V
FG output low voltage	IpG = 1.2 mA,	V _I = 2.8 V	-40°C to 125°C			0.4	l ^v

[†] CSR refers to the total series resistance, including the ESR of the capacitor, any series resistance added externally, and PWB trace resistance to C_O.



[‡] Pulse-testing techniques are used to maintain virtual junction temperature as close as possible to ambient temperature; thermal effects must be taken into account separately.

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TPS7248Q electrical characteristics, I_O = 10 mA, V_I = 5.85 V, $\overline{\text{EN}}$ = 0 V, C_O = 4.7 μF (CSR[†] = 1 Ω), SENSE shorted to OUT (unless otherwise noted)

DADAMETER	TEST 001	DITIONST	_	TPS7248Q			
PARAMETER	TEST CON	DITIONS+	ТЈ	MIN	TYP	MAX	UNII
Output voltage	V _I = 5.85 V,	$I_O = 10 \text{ mA}$	25°C		4.85		V
Output voitage	$5.85 \text{ V} \le \text{V}_{I} \le 10 \text{ V},$	$5 \text{ mA} \le I_{\mbox{O}} \le 250 \text{ mA}$	-40°C to 125°C	4.75		4.95	V
	I _O = 10 mA,	V _I = 4.75 V	25°C		10	19	
	IO = 10 IIIA,	V = 4.75 V	-40°C to 125°C			30	
Dropout voltage	I _O = 100 mA,	V _I = 4.75 V	25°C		90	100	m\/
Dropout voltage	10 = 100 IIIA,	V = 4.75 V	-40°C to 125°C			150	1110
	I _O = 250 mA,	V _I = 4.75 V	25°C		216	250	
	10 = 250 IIIA,	V = 4.75 V	-40°C to 125°C			285	UNIT V MV MV MV MV MV MV WV W
Pass-element series resistance	(4.75 V – V _O)/I _O ,	V _I = 4.75 V,	25°C		0.8	1	0
Fass-element series resistance	$I_{O} = 250 \text{ mA}$		-40°C to 125°C			1.4	52
Innut requisition	V: 5.05.V to 10.V	50 ·· \ < \ < 050 ·· \	25°C			34	m)/
Input regulation	$V_I = 5.85 \text{ V to } 10 \text{ V},$	$50 \mu A \le I_O \le 250 mA$	-40°C to 125°C			50	IIIV
Output regulation		5.85 V ≤ V _I ≤ 10 V	25°C		43	55	
	$I_O = 5 \text{ mA to } 250 \text{ mA},$	5.05 V ≤ V ≤ 10 V	-40°C to 125°C			95	m\/
	In FO A to 050 mA	E 05 \\ < \\ < 40 \\	25°C		55	75	IIIV
	$I_O = 50 \mu\text{A} \text{ to } 250 \text{mA},$	5.05 V ≤ V ≤ 10 V	-40°C to 125°C			135	
		In 50 A	25°C	42	53		
Dinnle rejection	f 120 H-	ΙΟ = 50 μΑ	-40°C to 125°C	36			чD
Ripple rejection	f = 120 Hz	1a 250 mA	25°C	36	46		иь
		I _O = 250 mA	-40°C to 125°C	34			
Output noise spectral density	f = 120 Hz		25°C		2		μV/√ Hz
		$C_O = 4.7 \mu F$	25°C		370		
Output noise voltage	10 Hz \leq f \leq 100 kHz, CSR [†] = 1 Ω	C _O = 10 μF	25°C		290		μVrms
	C3K1 = 1 22	C _O = 100 μF	25°C		168		
PG trip-threshold voltage	V _O voltage decreasing from above V _{PG}		-40°C to 125°C		0.95 × VO(nom)		V
PG hysteresis voltage			25°C		50		mV
DC systematic leaves related to	4.0 4	V 440V	25°C		0.2	0.4	.,
PG output low voltage	$I_{PG} = 1.2 \text{ mA},$	V _I = 4.12 V	-40°C to 125°C			0.4	v

[†] CSR refers to the total series resistance, including the ESR of the capacitor, any series resistance added externally, and PWB trace resistance to CO.

[‡] Pulse-testing techniques are used to maintain virtual junction temperature as close as possible to ambient temperature; thermal effects must be taken into account separately.

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TPS7250Q electrical characteristics, I $_{O}$ = 10 mA, V $_{I}$ = 6 V, \overline{EN} = 0 V, C $_{O}$ = 4.7 μF (CSR † = 1 Ω), SENSE shorted to OUT (unless otherwise noted)

DARAMETER	TEOT 001	IDITIONS [†]	TPS7250Q			UNIT	
PARAMETER	TEST CON	IDITIONS+	TJ	MIN	TYP	MAX	UNII
Output voltage	V _I = 6 V,	I _O = 10 mA	25°C		5		V
Output voltage	$6 \text{ V} \le \text{V}_{I} \le 10 \text{ V},$	$5~\text{mA} \leq I_{\mbox{O}} \leq 250~\text{mA}$	-40°C to 125°C	4.9		5.1	v
	IO = 10 mA,	V _I = 4.88 V	25°C		8	12	
	IO = 10 IIIA,	V = 4.00 V	-40°C to 125°C			30	
Dropout voltage	I _O = 100 mA,	V _I = 4.88 V	25°C		76	85	m\/
Dropout voltage	10 = 100 IIIA,	V = 4.00 V	-40°C to 125°C			136] '''V
	IO = 250 mA,	V _I = 4.88 V	25°C		190	206	30 85 36 206 312 225 225 28 35 MV 61 00 79
	10 = 250 IIIA,	V = 4.00 V	-40°C to 125°C			312	
Pass-element series resistance	(4.88 V – V _O)/I _O ,	V _I = 4.88 V,	25°C		0.76	0.825	
Pass-element series resistance	$I_O = 250 \text{ mA}$		-40°C to 125°C			1.25	22
lament required	Vi. 6.V to 10.V	50 A < 1 = < 250 mA	25°C			28	\/
Input regulation	$V_{I} = 6 V \text{ to } 10 V,$	$50 \mu\text{A} \le \text{I}_{\text{O}} \le 250 \text{mA}$	-40°C to 125°C			35	IIIV
Output regulation	I _O = 5 mA to 250 mA,	6 \ / < \ / < 10 \ /	25°C		46	61	
	10 = 3 mA to 230 mA,	0 V \(\sqrt{10 V}	-40°C to 125°C			100	m\/
	$I_{O} = 50 \mu\text{A} \text{ to } 250 \text{mA},$	6 // < // < 10 //	25°C		59 79	1117	
	$10 = 30 \mu\text{A} \text{ to } 250 \text{mA},$	0 V \(\sqrt{10 V}	-40°C to 125°C			150	
		ΙΟ = 50 μΑ	25°C	41	52		
Dinale rejection	f = 120 Hz	ΙΟ = 50 μΑ	-40°C to 125°C	37			40
Ripple rejection	I = 120 HZ	1- 250 mA	25°C	36	46		uБ
		I _O = 250 mA	-40°C to 125°C	32			
Output noise spectral density	f = 120 Hz		25°C		2		μV/√Hz
		C _O = 4.7 μF	25°C		390		
Output noise voltage	10 Hz \leq f \leq 100 kHz, CSR [†] = 1 Ω	C _O = 10 μF	25°C		300		μVrms
	051(1 = 1 52	C _O = 100 μF	25°C		175		1
PG trip-threshold voltage	V _O voltage decreasing from above V _{PG}		-40°C to 125°C		$\begin{array}{c} 0.95 \times \\ \text{VO(nom)} \end{array}$		V
PG hysteresis voltage			25°C		50		mV
PC output low voltage	Ino - 1 2 m/	\/ı = 4.25.\/	25°C		0.19	0.4	V
PG output low voltage	$I_{PG} = 1.2 \text{ mA},$	V _I = 4.25 V	-40°C to 125°C			0.4	l ^v

[†] CSR refers to the total series resistance, including the ESR of the capacitor, any series resistance added externally, and PWB trace resistance to CO.

[‡] Pulse-testing techniques are used to maintain virtual junction temperature as close as possible to ambient temperature; thermal effects must be taken into account separately.

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electrical characteristics, I_O = 10 mA, \overline{EN} = 0 V, C_O = 4.7 μF (CSR[†] = 1 Ω), T_J = 25°C, SENSE/FB shorted to OUT (unless otherwise noted)

PARAMETER	TEST CONDITIONS‡	TPS72xxY	UNIT
PARAMETER	TEST CONDITIONS+	MIN TYP MAX	
Ground current (active mode)	$\overline{\text{EN}} \le 0.5 \text{ V}, \qquad V_{\text{I}} = V_{\text{O}} + 1 \text{ V}, \\ 0 \text{ mA} \le I_{\text{O}} \le 250 \text{ mA}$	180	μА
Output current limit threshold	$V_0 = 0 \text{ V}, \qquad V_1 = 10 \text{ V}$	0.6	А
Thermal shutdown junction temperature		165	°C
EN hysteresis voltage		50	mV
Minimum V _I for active pass element		1.9	V
Minimum V _I for valid PG	IpG = 300 μA	1.1	V

electrical characteristics, I $_{O}$ = 10 mA, \overline{EN} = 0 V, C $_{O}$ = 4.7 μF (CSR † = 1 Ω), T $_{J}$ = 25°C, FB shorted to OUT at device leads (unless otherwise noted)

PARAMETER	TEST 00	NDITIONS‡	TF	TPS7201Y		
PARAMETER	lesi co	NDITION5+	MIN	TYP	MAX	UNIT
Reference voltage (measured at FB with OUT connected to FB)	V _I = 3.5 V,	I _O = 10 mA		1.188		V
	V _I = 2.4 V,§	$50 \ \mu A \le I_O \le 100 \ mA$		2.1		
	V _I = 2.4 V,§	$100~\text{mA} \leq I_{\mbox{\scriptsize O}} \leq 200~\text{mA}$		2.9		
Pass-element series resistance (see Note 3)	V _I = 2.9 V,	$50~\mu\text{A} \leq I_{\mbox{O}} \leq 250~m\text{A}$		1.6		Ω
	V _I = 3.9 V,	$50~\mu\text{A} \leq I_O \leq 250~\text{mA}$		1		
	V _I = 5.9 V,	$50~\mu\text{A} \leq \text{I}_{\mbox{O}} \leq 250~\text{mA}$		0.8		
Output regulation	$3 \text{ V} \le \text{V}_{\text{I}} \le 10 \text{ V},$ See Note 2	$I_O = 5$ mA to 250 mA,	15			
	$3 \text{ V} \le \text{V}_{\text{I}} \le 10 \text{ V},$ See Note 2	I_{O} = 50 μ A to 250 mA,		17		mV
	V. 25V	ΙΟ = 50 μΑ		60		
Ripple rejection	V _I = 3.5 V, f = 120 Hz	I _O = 250 mA, See Note 2		50		dB
Output noise spectral density	V _I = 3.5 V,	f = 120 Hz		2		μV/√ Hz
	V _I = 3.5 V,	$C_O = 4.7 \mu F$		235		
Output noise voltage	10 Hz ≤ f ≤ 100 kHz,	C _O = 10 μF		190		μVrms
	$CSR^{\dagger} = 1 \Omega$	C _O = 100 μF		125		
PG hysteresis voltage¶	V _I = 3.5 V,	Measured at VFB		12		mV
PG output low voltage¶	V _I = 2.13 V,	I _{PG} = 400 μA		0.1		V
FB input current	V _I = 3.5 V			0.1		nA

TCSR refers to the total series resistance, including the ESR of the capacitor, any series resistance added externally, and PWB trace resistance

 $V_{DO} = I_O \cdot r_{DS(on)}$

 $r_{DS(on)}$ is a function of both output current and input voltage. The parametric table lists $r_{DS(on)}$ for $V_I = 2.4 \text{ V}$, 2.9 V, 3.9 V, and 5.9 V, which corresponds to dropout conditions for programmed output voltages of 2.5 V, 3 V, 4 V, and 6 V, respectively. For other programmed values, refer to Figures 10 and 11.



[‡] Pulse-testing techniques are used to maintain virtual junction temperature as close as possible to ambient temperature; thermal effects must be taken into account separately.

[§] This voltage is not recommended.

 $[\]P$ Output voltage programmed to 2.5 V with closed-loop configuration (see application information).

NOTES: 2 When V_I < 2.9 V and I_O > 100 mA simultaneously, pass element r_{DS(on)} increases (see Figure 10) to a point such that the resulting dropout voltage prevents the regulator from maintaining the specified tolerance range.

³ To calculate dropout voltage, use equation:

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electrical characteristics, I $_{O}$ = 10 mA, \overline{EN} = 0 V, C $_{O}$ = 4.7 μF (CSR † = 1 Ω), T $_{J}$ = 25 °C, FB shorted to OUT at device leads (unless otherwise noted)

DADAMETER	TEOT 00	NOTIONOT	TPS7225Y			UNIT
PARAMETER	IEST CO	NDITIONS [‡]	MIN	TYP	MAX	UNII
Output voltage	V _I = 3.5 V,	I _O = 10 mA		2.5		V
Dropout voltage	V _I = 2.97 V,	I _O = 250 mA		560		mV
Pass-element series resistance	$(2.97 \text{ V} - \text{V}_{\text{O}})/\text{I}_{\text{O}},$ $\text{I}_{\text{O}} = 250 \text{ mA}$	V _I = 2.97 V,		2.24		Ω
Input regulation	$V_I = 3.5 \text{ V to } 10 \text{ V},$	$50 \mu A \le I_O \le 250 mA$		9		mV
Output regulation	$3.5 \text{ V} \le \text{V}_{\text{I}} \le 10 \text{ V}$	I _O = 5 mA to 250 mA		28		\/
	$3.5 \text{ V} \leq \text{V}_{I} \leq 10 \text{ V}$	$I_0 = 50 \mu\text{A} \text{ to } 250 \text{mA}$		24		mV
Pinnle rejection	V _I = 3.5 V,	ΙΟ = 50 μΑ		58		dB
Ripple rejection	f = 120 Hz	I _O = 250 mA		46		иь
Output noise spectral density	V _I = 3.5 V,	f = 120 Hz		2		μV/√Hz
	V _I = 3.5 V,	C _O = 4.7 μF		248		
Output noise voltage	10 Hz ≤ f ≤ 100 kHz,	C _O = 10 μF		200		μVrms
	$CSR^{\dagger} = 1 \Omega$	C _O = 100 μF		130		
PG hysteresis voltage	V _I = 3.5 V			50		mV
PG output low voltage	V _I = 2.13 V	Ipg = 1.2 mA		0.3		V

[†] CSR refers to the total series resistance, including the ESR of the capacitor, any series resistance added externally, and PWB trace resistance



[‡] Pulse-testing techniques are used to maintain virtual junction temperature as close as possible to ambient temperature; thermal effects must be taken into account separately.

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electrical characteristics, I $_{O}$ = 10 mA, \overline{EN} = 0 V, C $_{O}$ = 4.7 μF (CSR † = 1 Ω), T $_{J}$ = 25 $^{\circ}$ C, SENSE shorted to OUT (unless otherwise noted) (continued)

PARAMETER	TEST C	ONDITIONS‡	Т	PS7228	1	UNIT
PARAMETER	TEST CO	TADITIONS+	MIN	TYP	MAX	UNIT
Output voltage	V _I = 3.75 V,	$I_O = 10 \text{ mA}$		2.75		V
	V _I = 2.97 V,	$I_O = 10 \text{ mA}$		TBD		
Dropout voltage	V _I = 2.97 V,	I _O = 100 mA		TBD		mV
	V _I = 2.97 V,	I _O = 250 mA		TBD		
Pass-element series resistance	$(2.97 \text{ V} - \text{V}_{\text{O}})/\text{I}_{\text{O}},$ $\text{I}_{\text{O}} = 250 \text{ mA}$	V _I = 2.97 V,		TBD		Ω
Input regulation	$V_I = 3.75 \text{ V to } 10 \text{ V},$	$50 \ \mu\text{A} \le I_{\mbox{O}} \le 250 \ \mbox{mA}$		TBD		mV
Output regulation	$3.75 \text{ V} \le \text{V}_{\text{I}} \le 10 \text{ V},$	I _O = 5 mA to 250 mA		TBD		mV
Output regulation	$3.75 \text{ V} \le \text{V}_{\text{I}} \le 10 \text{ V},$	$I_{O} = 50 \mu\text{A}$ to 250 mA		TBD		IIIV
Ripple rejection	V _I = 3.75 V,	ΙΟ = 50 μΑ		TBD		dB
Rippie rejection	f = 120 Hz	I _O = 250 mA		TBD		uБ
Output noise spectral density	V _I = 3.75 V,	f = 120 Hz		TBD		μV/√ Hz
	V _I = 3.75 V,	$C_{O} = 4.7 \mu\text{F}$		TBD		
Output noise voltage	10 Hz ≤ f ≤ 100 kHz,	C _O = 10 μF		TBD		μVrms
ON	$CSR^{\dagger} = 1 \Omega$	C _O = 100 μF		TBD		
PG hysteresis voltage	V _I = 3.75 V	_		TBD		mV
PG output low voltage	V _I = 2.34 V,	Ipg = 1.2 mA		TBD		V

[†]CSR refers to the total series resistance, including the ESR of the capacitor, any series resistance added externally, and PWB trace resistance

[‡] Pulse-testing techniques are used to maintain virtual junction temperature as close as possible to ambient temperature; thermal effects must be taken into account separately.

PARAMETER	TEST CO.	NDITIONS‡	TPS7230Y			UNIT
PARAMETER	TEST CO	NDITION5+	MIN	TYP	MAX	UNII
Output voltage	V _I = 4 V,	I _O = 10 mA		3		V
Desmontrueltono	V _I = 2.97 V,	I _O = 100 mA		145		mV
Dropout voltage	V _I = 2.97 V,	I _O = 250 mA		390		IIIV
Pass-element series resistance	$(2.97 \text{ V} - \text{V}_{\text{O}})/\text{I}_{\text{O}},$ $\text{I}_{\text{O}} = 250 \text{ mA}$	V _I = 2.97 V,		1.56		Ω
Input regulation	V _I = 4 V to 10 V,	$50~\mu\text{A} \leq I_{\mbox{O}} \leq 250~\text{mA}$		9		mV
Output regulation	4 V ≤ V _I ≤ 10 V	I _O = 5 mA to 250 mA	34			mV
	4 V ≤ V _I ≤ 10 V	$I_0 = 50 \mu A \text{ to } 250 \text{ mA}$		41		mv
Ripple rejection	V _I = 4 V,	ΙΟ = 50 μΑ		56		dB
Rippie rejection	f = 120 Hz	I _O = 250 mA		45		uБ
Output noise spectral density	V _I = 4 V,	f = 120 Hz		2		μV/√ Hz
	V _I = 4 V,	$C_O = 4.7 \mu F$		256		
Output noise voltage	10 Hz \leq f \leq 100 kHz,	C _O = 10 μF		206		μVrms
	$CSR^{\dagger} = 1 \Omega$	C _O = 100 μF		132		
PG hysteresis voltage	V _I = 4 V			50		mV
PG output low voltage	V _I = 2.55 V	IpG = 1.2 mA		0.25		V

[†] CSR refers to the total series resistance, including the ESR of the capacitor, any series resistance added externally, and PWB trace resistance

[‡] Pulse-testing techniques are used to maintain virtual junction temperature as close as possible to ambient temperature; thermal effects must be taken into account separately.



electrical characteristics, I $_{O}$ = 10 mA, \overline{EN} = 0 V, C $_{O}$ = 4.7 μF (CSR † = 1 Ω), T $_{J}$ = 25 °C, SENSE shorted to OUT (unless otherwise noted) (continued)

DADAMETED	TECT O	ONDITIONS‡	Т	TPS7233Y MIN TYP MAX		
PARAMETER	IESI C	UNDITIONS+	MIN			
Output voltage	$V_{I} = 4.3 V$,	$I_O = 10 \text{ mA}$		3.3		V
	V _I = 3.23 V,	$I_O = 10 \text{ mA}$		14		
Dropout voltage	V _I = 3.23 V,	I _O = 100 mA		140		mV
	V _I = 3.23 V,	I _O = 250 mA		360		
Pass-element series resistance	$(3.23 \text{ V} - \text{V}_{\text{O}})/\text{I}_{\text{O}},$ $\text{I}_{\text{O}} = 250 \text{ mA}$	V _I = 3.23 V,		1.5		Ω
Input regulation	$V_I = 4.3 \text{ V to } 10 \text{ V},$	$50 \mu A \le I_O \le 250 mA$		8		mV
Output regulation	$4.3 \text{ V} \le \text{V}_{\text{I}} \le 10 \text{ V},$	$I_O = 5$ mA to 250 mA		32		\/
Output regulation	$4.3 \text{ V} \le \text{V}_{I} \le 10 \text{ V},$	$I_O = 50 \mu\text{A}$ to 250 mA		41		mV
Ripple rejection	V _I = 4.3 V,	ΙΟ = 50 μΑ		52		dB
Rippie rejection	f = 120 Hz	I _O = 250 mA		44		иь
Output noise spectral density	V _I = 4.3 V,	f = 120 Hz		2		μV/√ Hz
	V _I = 4.3 V,	$C_{O} = 4.7 \mu F$		265		
Output noise voltage	10 Hz \leq f \leq 100 kHz,	C _O = 10 μF		212		μVrms
	$CSR^{\dagger} = 1 \Omega$	$T = 1 \Omega$ $C_O = 100 \mu\text{F}$ 135		135		
PG hysteresis voltage	V _I = 4.3 V			32		mV
PG output low voltage	V _I = 2.8 V,	I _{PG} = 1.2 mA		0.22		V

[†] CSR refers to the total series resistance, including the ESR of the capacitor, any series resistance added externally, and PWB trace resistance

[‡] Pulse-testing techniques are used to maintain virtual junction temperature as close as possible to ambient temperature; thermal effects must be taken into account separately.

DADAMETER	TEOT 00	NDITIONST	TPS7248Y			UNIT
PARAMETER	IESI CO	NDITIONS [‡]	MIN	TYP	MAX	UNII
Output voltage	V _I = 5.85 V,	I _O = 10 mA		4.85		V
	V _I = 4.75 V,	I _O = 10 mA		10		
Dropout voltage	V _I = 4.75 V,	I _O = 100 mA		90		mV
	V _I = 4.75 V,	$I_O = 250 \text{ mA}$		216		
Pass-element series resistance	$(4.75 \text{ V} - \text{V}_{\text{O}})/\text{I}_{\text{O}},$ $\text{I}_{\text{O}} = 250 \text{ mA}$	V _I = 4.75 V,		0.8		Ω
Output regulation	5.85 V ≤ V _I ≤ 10 V	I _O = 5 mA to 250 mA		43		\/
	5.85 V ≤ V _I ≤ 10 V	$I_O = 50 \mu A \text{ to } 250 \text{ mA}$		55		mV
Binnle rejection	V _I = 5.85 V,	I _O = 50 μA		53		dB
Ripple rejection	f = 120 Hz	I _O = 250 mA		46		uБ
Output noise spectral density	V _I = 5.85 V,	f = 120 Hz		2		μV/√ Hz
	V _I = 5.85 V,	C _O = 4.7 μF		370		
Output noise voltage	10 Hz ≤ f ≤ 100 kHz,	C _O = 10 μF		290		μVrms
	$CSR^{\dagger} = 1 \Omega$	C _O = 100 μF		168		
PG hysteresis voltage	V _I = 5.85 V			50		mV
PG output low voltage	V _I = 4.12 V	Ipg = 1.2 mA		0.2		V

[†] CSR refers to the total series resistance, including the ESR of the capacitor, any series resistance added externally, and PWB trace resistance

[‡] Pulse-testing techniques are used to maintain virtual junction temperature as close as possible to ambient temperature; thermal effects must be taken into account separately.



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electrical characteristics, I $_{O}$ = 10 mA, \overline{EN} = 0 V, C $_{O}$ = 4.7 μF (CSR † = 1 Ω), T $_{J}$ = 25 °C, SENSE shorted to OUT (unless otherwise noted) (continued)

PARAMETER	TEST CO	NDITIONS‡	TPS7250Y			UNIT
PARAMETER	IEST CO	NDITIONS+	MIN	TYP	MAX	UNIT
Output voltage	V _I = 6 V,	$I_O = 10 \text{ mA}$		5		V
	V _I = 4.88 V	$I_O = 10 \text{ mA}$		8		
Dropout voltage	V _I = 4.88 V	$I_0 = 100 \text{ mA}$		76		mV
	V _I = 4.88 V,	$I_0 = 250 \text{ mA}$		190		
Pass-element series resistance	$(4.88 \text{ V} - \text{V}_{\text{O}})/\text{I}_{\text{O}},$ $\text{I}_{\text{O}} = 250 \text{ mA}$	V _I = 4.88 V,		0.76		Ω
Input regulation	$V_I = 6 V \text{ to } 10 V,$	$50 \ \mu\text{A} \le I_{\mbox{O}} \le 250 \ \mbox{mA}$				mV
Output regulation	6 V ≤ V _I ≤ 10 V,	$I_O = 5$ mA to 250 mA		46		m\/
Output regulation	6 V ≤ V _I ≤ 10 V,	$I_{O} = 50 \mu\text{A}$ to 250 mA		59		mV
Dipple rejection	V _I = 6 V,	ΙΟ = 50 μΑ		52		dB
Ripple rejection	f = 120 Hz	I _O = 250 mA		46		uБ
Output noise spectral density	V _I = 6 V,	f = 120 Hz		2		μV/√ Hz
	V _I = 6 V,	C _O = 4.7 μF		390		
Output noise voltage	10 Hz \leq f \leq 100 kHz,	C _O = 10 μF		300		μVrms
	$CSR^{\dagger} = 1 \Omega$	C _O = 100 μF		175		
PG hysteresis voltage	V _I = 6 V			50		mV
PG output low voltage	V _I = 4.25 V,	Ipg = 1.2 mA		0.19		V

[†]CSR refers to the total series resistance, including the ESR of the capacitor, any series resistance added externally, and PWB trace resistance to CO.

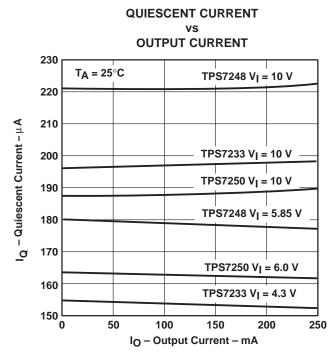


[‡] Pulse-testing techniques are used to maintain virtual junction temperature as close as possible to ambient temperature; thermal effects must be taken into account separately.

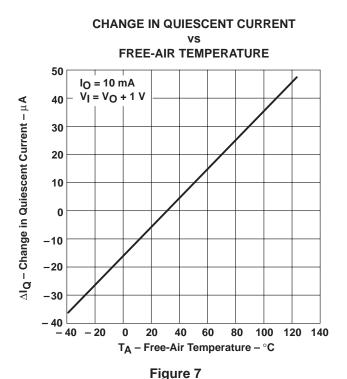
Table of Graphs

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IQ	Quiescent current	vs Input voltage	6
ΔI_Q^{\dagger}	Change in quiescent current	vs Free-air temperature	7
V_{DO}	Dropout voltage	vs Output current	8
ΔV_{DO}	Change in dropout voltage	vs Free-air temperature	9
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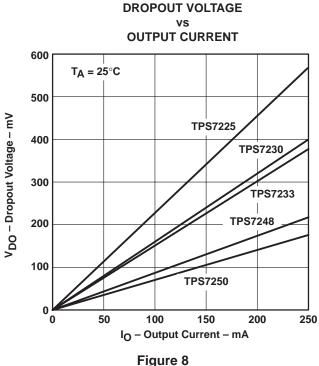
[†] This symbol is not currently listed within EIA or JEDEC standards for semiconductor symbology.



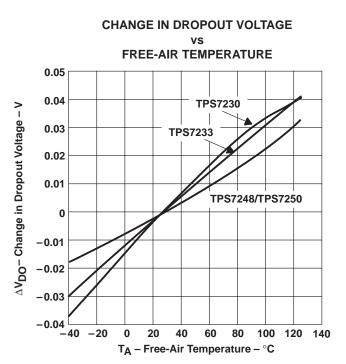




QUIESCENT CURRENT INPUT VOLTAGE 250 **TPS7248** T_A 25°C $I_0 = 250 \text{ mA}$ **TPS7233** 200 IQ - Quiescent Current - μA 150 TPS7201 With VO Programmed to 2.5 V 100 **TPS7250** 50 0 2 5 6 8 9 10 V_I - Input Voltage - V Figure 6





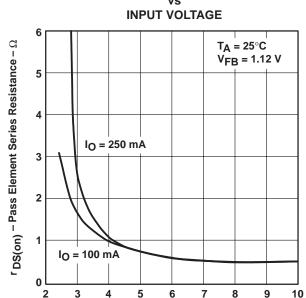


TPS7201 DROPOUT VOLTAGE vs **OUTPUT CURRENT** 1.6 $V_1 = 2.4 V^{\dagger}$ 1.4 1.2 V_{DO} - Dropout Voltage - V $V_{I} = 2.6 V^{\dagger}$ $V_{I} = 2.9 V$ 1 $V_{I} = 3.2 \text{ V}$ $V_{I} = 3.9 V$ 0.8 $V_{I} = 5.9 V$ 0.6 $V_{I} = 9.65 V$ 0.4 0.2 50 100 150 200 250 IO - Output Current - mA

† This voltage is not recommended.

Figure 9

PASS ELEMENT SERIES RESISTANCE



V_I - Input Voltage - V

Figure 11

CHANGE IN OUTPUT VOLTAGE

Figure 10

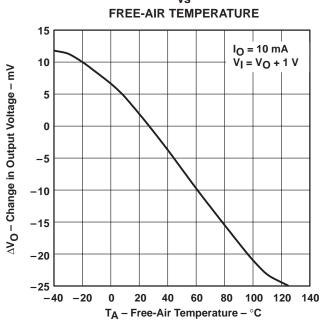


Figure 12

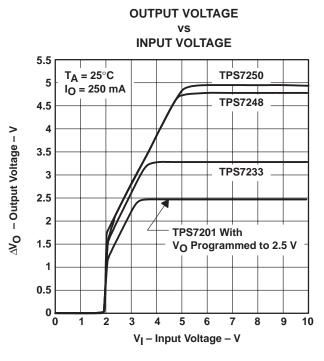


Figure 13

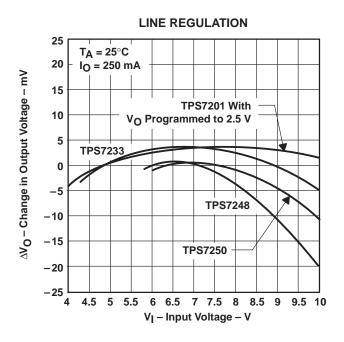


Figure 14

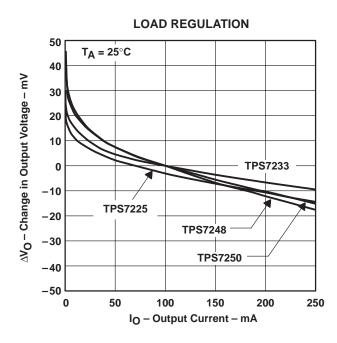
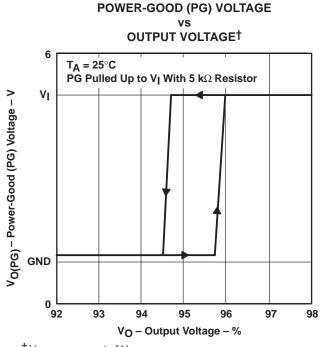


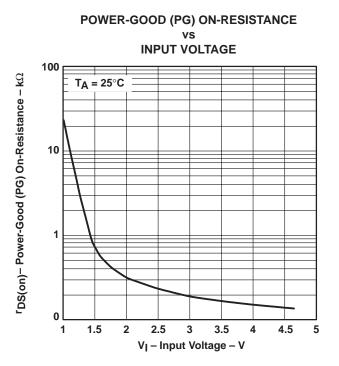
Figure 15



†VO as a percent of VOnom.

Figure 16





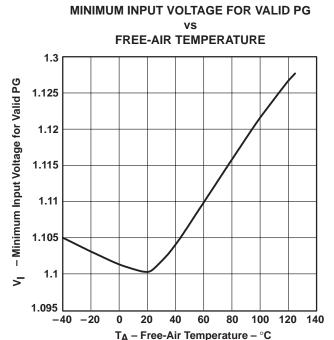


Figure 17

Figure 18

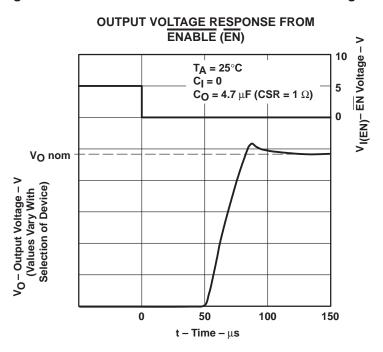


Figure 19

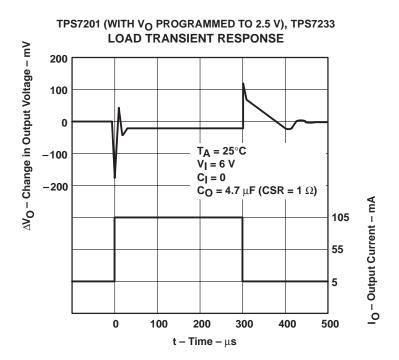


Figure 20

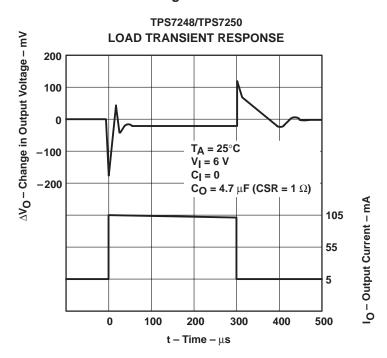


Figure 21



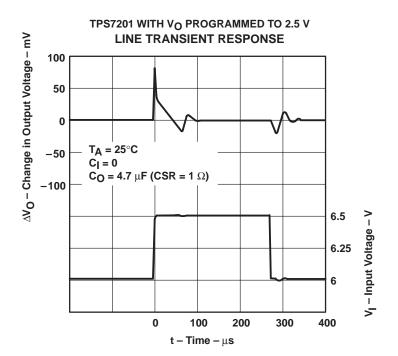


Figure 22

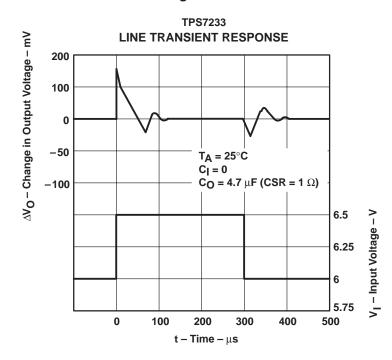


Figure 23

TYPICAL CHARACTERISTICS

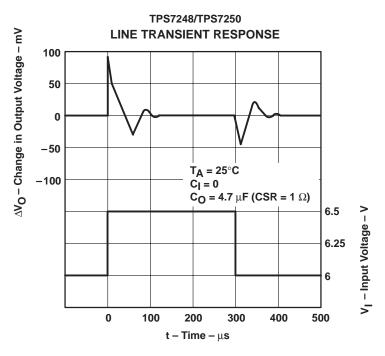
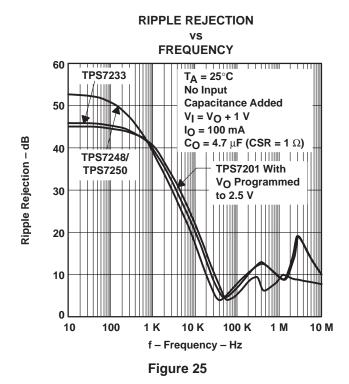


Figure 24



FREQUENCY 10 T_A = 25°C Output Spectral Noise Density – μ V/ $\sqrt{\text{Hz}}$ No Input Capacitance Added $V_I = V_O + 1 V$ $C_0 = 4.7 \,\mu\text{F} \,(\text{CSR} = 1 \,\Omega)$ $C_0 = 10 \mu F (CSR = 1 \Omega)$ $C_0 = 100 \, \mu F \, (CSR = 1 \, \Omega)$ 0.01 10 100 k 1 k 10 k

f - Frequency - Hz

Figure 26

OUTPUT SPECTRAL NOISE DENSITY

TYPICAL REGIONS OF STABILITY COMPENSATION SERIES RESISTANCE (CSR)† vs

OUTPUT CURRENT

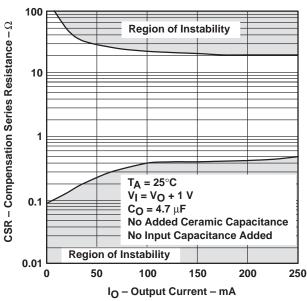
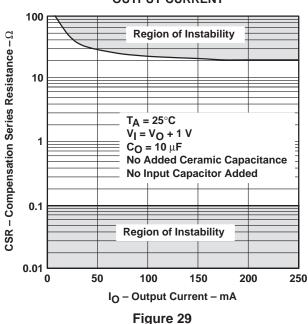


Figure 27

TYPICAL REGIONS OF STABILITY COMPENSATION SERIES RESISTANCE (CSR)†

vs OUTPUT CURRENT



TYPICAL REGIONS OF STABILITY COMPENSATION SERIES RESISTANCE (CSR)†

vs ADDED CERAMIC CAPACITANCE

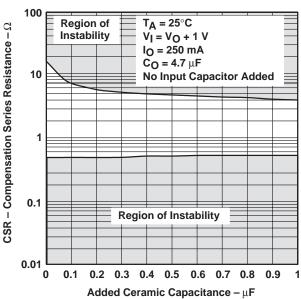


Figure 28

TYPICAL REGIONS OF STABILITY COMPENSATION SERIES RESISTANCE (CSR)[†]

ADDED CERAMIC CAPACITANCE

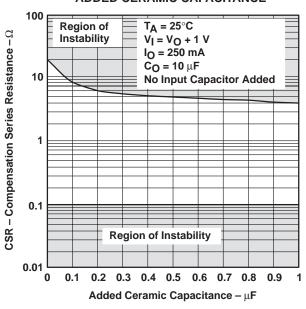


Figure 30

[†] CSR refers to the total series resistance, including the ESR of the capacitor, any series resistance added externally, and PWB trace resistance to C_O.



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APPLICATION INFORMATION

The design of the TPS72xx family of low-dropout (LDO) regulators is based on the higher-current TPS71xx family. These new families of regulators have been optimized for use in battery-operated equipment and feature extremely low dropout voltages, low supply currents that remain constant over the full-output-current range of the device, and an enable input to reduce supply currents to less than $0.5 \,\mu\text{A}$ when the regulator is turned off.

device operation

The TPS72xx uses a PMOS pass element to dramatically reduce both dropout voltage and supply current over more conventional PNP-pass-element LDO designs. The PMOS transistor is a voltage-controlled device that, unlike a PNP transistor, does not require increased drive current as output current increases. Supply current in the TPS72xx is essentially constant from no-load to maximum.

Current limiting and thermal protection prevent damage by excessive output current and/or power dissipation. The device switches into a constant-current mode at approximately 1 A; further load increases reduce the output voltage instead of increasing the output current. The thermal protection shuts the regulator off if the junction temperature rises above 165°C. Recovery is automatic when the junction temperature drops approximately 5°C below the high temperature trip point. The PMOS pass element includes a back diode that safely conducts reverse current when the input voltage level drops below the output voltage level.

A logic high on the enable input, $\overline{\text{EN}}$, shuts off the output and reduces the supply current to less than 0.5 μ A. $\overline{\text{EN}}$ should be grounded in applications where the shutdown feature is not used.

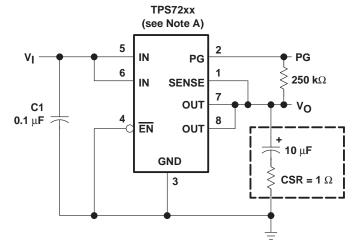
Power good (PG) is an open-drain output signal used to indicate output-voltage status. A comparator circuit continuously monitors the output voltage. When the output drops to approximately 95% of its nominal regulated value, the comparator turns on and pulls PG low.

Transient loads or line pulses can also cause activation of PG if proper care is not taken in selecting the input and output capacitors. Load transients that are faster than 5 μ s can cause a signal on PG if high-ESR output capacitors (greater than approximately 7 Ω) are used. A 1- μ s transient causes a PG signal when using an output capacitor with greater than 3.5 Ω of ESR. It is interesting to note that the output-voltage spike during the transient can drop well below the reset threshold and still not trip if the transient duration is short. A 1- μ s transient must drop at least 500 mV below the threshold before tripping the PG circuit. A 2- μ s transient trips PG at just 400 mV below the threshold. Lower-ESR output capacitors help by reducing the drop in output voltage during a transient and should be used when fast transients are expected.

A typical application circuit is shown in Figure 31.



APPLICATION INFORMATION



NOTE A: TPS7225, TPS7228[†], TPS7230, TPS7233, TPS7248, TPS7250 (fixed-voltage options).

Figure 31. Typical Application Circuit

external capacitor requirements

Although not required, a 0.047- μ F to 0.1- μ F ceramic bypass input capacitor, connected between IN and GND and located close to the TPS72xx, is recommended to improve transient response and noise rejection. A higher-value electrolytic input capacitor may be necessary if large, fast-rise-time load transients are anticipated and the device is located several inches from the power source.

An output capacitor is required to stabilize the internal feedback loop. For most applications, a $10-\mu F$ to $15-\mu F$ solid-tantalum capacitor with a $0.5-\Omega$ resistor (see capacitor selection table) in series is sufficient. The maximum capacitor ESR should be limited to $1.3~\Omega$ to allow for ESR doubling at cold temperatures. Figure 32 shows the transient response of a 5-mA to 85-mA load using a $10-\mu F$ output capacitor with a total ESR of $1.7~\Omega$.

A 4.7- μ F solid-tantalum capacitor in series with a 1- Ω resistor may also be used (see Figures 27 and 28) provided the ESR of the capacitor does not exceed 1 Ω at room temperature and 2 Ω over the full operating temperature range.

[†] This device is in the product preview stage of development. Please contact the local TI sales office for availability.

APPLICATION INFORMATION

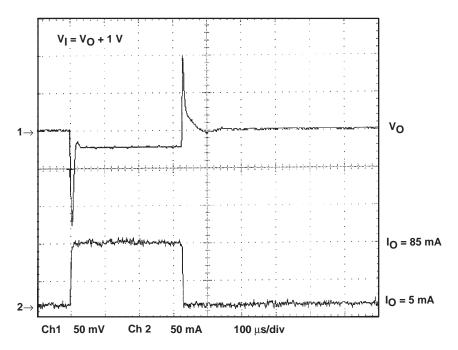


Figure 32. Load Transient Response (CSR total = 1.7 Ω), TPS7248Q

A partial listing of surface-mount capacitors usable with the TPS72xx family is provided below. This information (along with the stability graphs, Figures 27 through 30) is included to assist the designer in selecting suitable capacitors.

CAPACITOR SELECTION

PART NO.	MFR.	VALUE	MAX ESR†	SIZE $(H \times L \times W)^{\dagger}$
592D156X0020R2T	Sprague	15 μF, 20 V	1.1	$1.2\times7.2\times6$
595D156X0025C2T	Sprague	15 μ F, 25 V	1	$2.5\times7.1\times3.2$
595D106X0025C2T	Sprague	10 μ F, 25 V	1.2	$2.5\times7.1\times3.2$
695D106X0035G2T	Sprague	10 μ F, 35 V	1.3	$2.5\times7.6\times2.5$

[†] Size is in mm. ESR is maximum resistance in ohms at 100 kHz and $T_A = 25^{\circ}C$. Listings are sorted by height.

sense-pin connection

SENSE must be connected to OUT for proper operation of the regulator. Normally this connection should be as short as possible; however, remote sense may be implemented in critical applications when proper care of the circuit path is exercised. SENSE internally connects to a high-impedance wide-bandwidth amplifier through a resistor-divider network, and any noise pickup on the PCB trace will feed through to the regulator output. SENSE must be routed to minimize noise pickup. Filtering SENSE using an RC network is not recommended because of the possibility of inducing regulator instability.



APPLICATION INFORMATION

output voltage programming

The output voltage of the TPS7201 adjustable regulator is programmed using an external resistor divider as shown in Figure 33. The output voltage is calculated using:

$$V_{O} = V_{ref} \cdot \left(1 + \frac{R1}{R2}\right) \tag{1}$$

Where

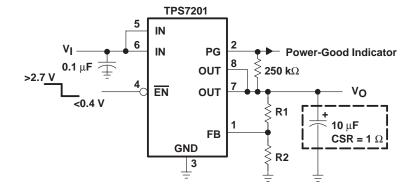
 $V_{ref} = 1.188 \text{ V}$ typ (the internal reference voltage)

Resistors R1 and R2 should be chosen for approximately 7- μ A divider current. Lower value resistors can be used but offer no inherent advantage and waste more power. Higher values should be avoided as leakage currents at FB increase the output voltage error. The recommended design procedure is to choose R2 = 169 k Ω to set the divider current at 7 μ A and then calculate R1 using:

$$R1 = \left(\frac{V_{O}}{V_{ref}} - 1\right) \cdot R2 \tag{2}$$

OUTPUT VOLTAGE PROGRAMMING GUIDE

OUTPUT VOLTAGE	DIVIDER RESISTANCE (kΩ)†		
(V)	R1	R2	
2.5	191	169	
3.3	309	169	
3.6	348	169	
4	402	169	
5	549	169	
6.4	750	169	



†1% values shown.

Figure 33. TPS7201 Adjustable LDO Regulator Programming

APPLICATION INFORMATION

power dissipation and junction temperature

Specified regulator operation is assured to a junction temperature of 125° C; the maximum junction temperature allowable to avoid damaging the device is 150° C. These restrictions limit the power dissipation that the regulator can handle in any given application. To ensure the junction temperature is within acceptable limits, calculate the maximum allowable dissipation, $P_{D(max)}$, and the actual dissipation, $P_{D,max}$, which must be less than or equal to $P_{D,max}$.

The maximum-power-dissipation limit is determined using the following equation:

$$P_{D(max)} = \frac{T_J max - T_A}{R_{\theta,JA}}$$

Where

T_Jmax is the maximum allowable junction temperature, i.e.,150°C absolute maximum and 125°C recommended operating temperature.

 $R_{\theta JA}$ is the thermal resistance junction-to-ambient for the package, i.e., 172°C/W for the 8-terminal SOIC and 238°C/W for the 8-terminal TSSOP.

T_A is the ambient temperature.

The regulator dissipation is calculated using:

$$P_{D} = (V_{I} - V_{O}) \cdot I_{O}$$

Power dissipation resulting from quiescent current is negligible.

regulator protection

The TPS72xx PMOS-pass transistor has a built-in back diode that safely conducts reverse currents when the input voltage drops below the output voltage (e.g., during power down). Current is conducted from the output to the input and is not internally limited. If extended reverse voltage is anticipated, external limiting might be appropriate.

The TPS72xx also features internal current limiting and thermal protection. During normal operation, the TPS72xx limits output current to approximately 1 A. When current limiting engages, the output voltage scales back linearly until the overcurrent condition ends. While current limiting is designed to prevent gross device failure, care should be taken not to exceed the power dissipation ratings of the package. If the temperature of the device exceeds 165°C, thermal-protection circuitry shuts it down. Once the device has cooled, regulator operation resumes.

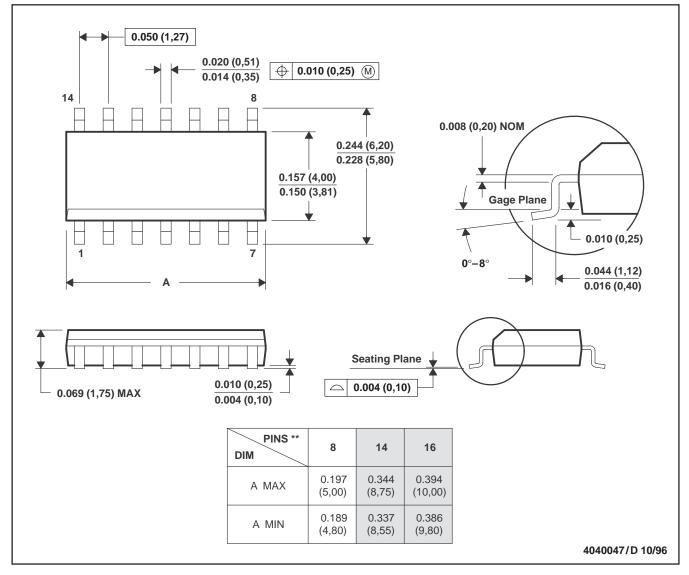


MECHANICAL DATA

D (R-PDSO-G**)

14 PIN SHOWN

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: B. All linear dimensions are in inches (millimeters).

C. This drawing is subject to change without notice.

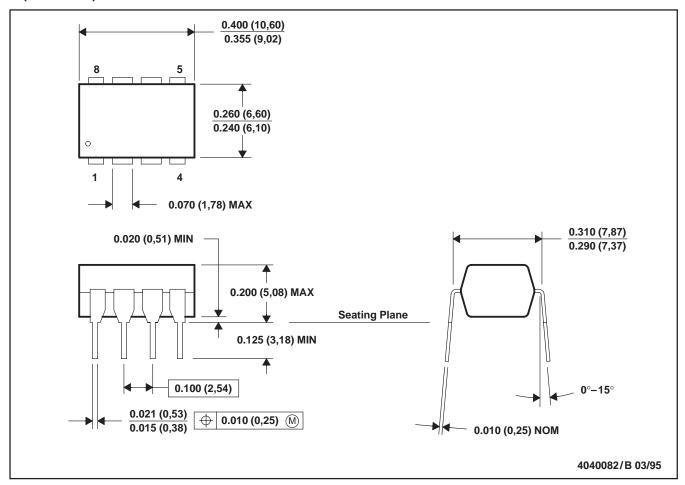
D. Body dimensions do not include mold flash or protrusion, not to exceed 0.006 (0,15).

E. Falls within JEDEC MS-012

MECHANICAL DATA

P (R-PDIP-T8)

PLASTIC DUAL-IN-LINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

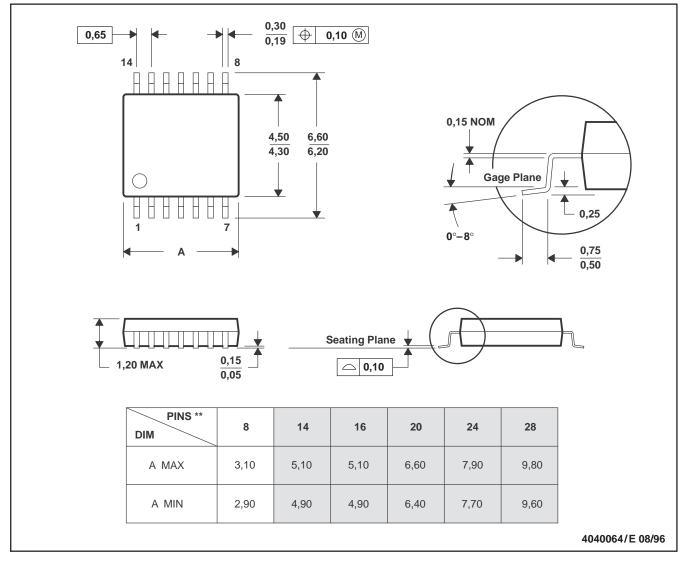
- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001

MECHANICAL DATA

PW (R-PDSO-G**)

14 PIN SHOWN

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.

D. Falls within JEDEC MO-153

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